M6MGB/T64BM34CWG

67,108,864-BIT (4,194,304-WORD BY 16-BIT) CMOS FLASH MEMORY & 33,554,432-BIT (2,097,152-WORD BY 16-BIT) CMOS MOBILE RAM

Stacked-CSP (Chip Scale Package)

Description

The M6MGB/T64BM34CWG is a Stacked Chip Scale Package (S-CSP) that contents 64M-bit Flash memory and 32M-bit Mobile RAM in a 67-pin Stacked CSP for lead free use.

64M-bit Flash memory is a 4,194,304 words, single power supply and high performance non-volatile memory fabricated by CMOS technology for the peripheral circuit and DINOR IV (Divided bit-line NOR IV) architecture for the memory cell. All memory blocks are locked and can not be programmed or erased, when F-WP# is Low. Using Software Lock Release function, program or erase operation can be executed.

32M-bit Mobile RAM is a 2,097,152 words high density RAM fabricated by CMOS technology for the peripheral circuit and DRAM cell for the memory array. The interface is compatible to an asynchronous SRAM.

The cells are automatically refreshed and the refresh control is not required for system. The device also has the partial block refresh scheme and the power down mode by writing the command.

The M6MGB/T64BM34CWG is suitable for a high performance cellular phone and a mobile PC that are required to be small mounting area, weight and small power dissipation.

Features

Access Time Flash 70ns (Max.)

Mobile RAM 80ns (Max.)

Supply Voltage F-VCC=M-VCC=2.7 ~ 3.0V

Ambient Temperature Ta=-40 ~ 85 degree

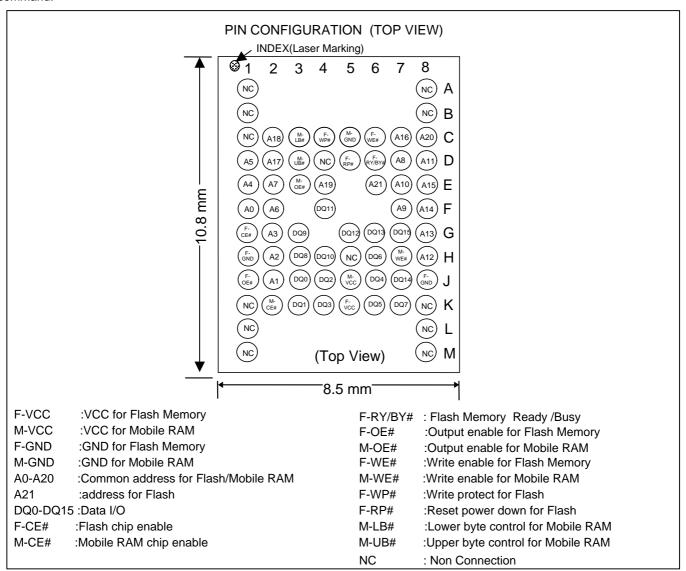
Package 67pin S-CSP

Ball pitch 0.80mm

Outer-ball:Su-Ag-Cu

Application

Mobile communication products

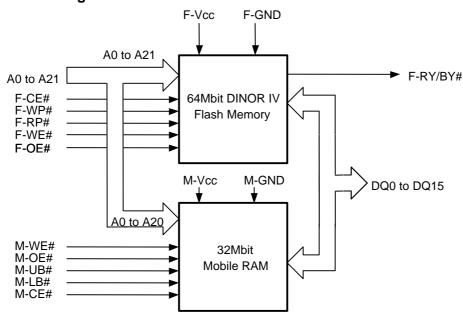


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MCP Block Diagram



Note: In the data sheet there are "VCC"s, "GND"s, "OE"s and "WE"s.

In the Flash Memory part they mean F-Vcc, F-GND, F-OE# and F-WE#.

In the Mobile RAM part they mean M-Vcc, M-GND, M-OE# and M-WE#.

In the Mobile RAM part UB# and LB# are M-UB# and M-LB#, respectively.

Capacitance

Symbol	Parameter		Conditions	Limits			Unit
Cymbol				Min.	Тур.	Max.	Onic
CIN	Input	A21-A0, F-OE#, F-WE#, F-CE#, F-WP#, F-	Ta=25°C, f=1MHz, Vin=Vout=0V			18	pF
	capacitance	RP#, M-CE#, M-OE#, M-WE#, M-LB#, M-UB#				_ 10	
COUT	Output	DQ15-DQ0, F-RY/BY#				22	pF
	Capacitance						

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Keep safety first in your circuit designs!

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